

## **IN THE SPECIFICATION**

### **Brief Description of the Drawings**

Applicants herewith submit one (1) replacement paragraph [0013] for the specification on the following page.

The replacement paragraph is added in connection with the addition of the new sheets of drawings.

No new matter has been added.

Applicants respectfully request the Examiner to enter the replacement paragraph [0013] for the specification.

[0013]        **Figure 6** is a graph illustrating one embodiment of a reflectivity wavelength for a ML mirror while **Figures 7A-7D** illustrate bi-layers located over a substrate in a broad-angle multilayer (ML) mirror or multiple layer structure.

### **Detailed Description**

Applicants herewith submit one (1) replacement paragraph [0026] for the detailed description of the specification on the following page.

The replacement paragraph is added in connection with the addition of the new sheets of drawings.

No new matter has been added.

Applicants respectfully request the Examiner to enter the replacement paragraph [0026] for the specification.

[0026] Based on the characteristics of the broad-angle ML mirror, pupil apodizations and phase shifts at the extreme angles will be reduced if mirror M3 shown in the system of **Figure 1** were replaced with the broad-angle ML mirror described in **Table 1**. In an embodiment of the present invention, a broad-angle multilayer (ML) mirror may include a multiple layer structure to provide uniform reflectivity over a wide range of incident angles with small phase shifts. In an embodiment of the present invention, the ML mirror or structure may include 36 bi-layers. As shown in an embodiment of the present invention in **Figures 7A-7D**, the bi-layers in the ML mirror or structure may have a variable thickness in different portions 710, 720, 730, over a substrate 700 of the ML mirror or structure. In an embodiment of the present invention as shown in **Table 1**, the bi-layer may include Molybdenum (Mo) with a thickness of 2.4 - 11.3 nm and Silicon (Si) with a thickness of 3.6 - 10.4 nm. In another embodiment of the present invention as shown in **Table 1**, Molybdenum may have a thickness of 2.4 - 3.7 nm except for a thicker bi-layer 1 located adjacent or nearest to the substrate and Silicon may have a thickness of 3.5 - 4.1 nm except for thicker bi-layers 3, 5, and 15 located farther from the substrate. In another embodiment of the present invention, the ML mirror or structure may include additional bi-layers. More than thirty-six bi-layers may be located over the substrate. The additional bi-layers may include Mo/Si bi-layers. The additional bi-layers may have a variable thickness.